

Appl. No. 10/031,526
Att. Docket No. 10191/2231
Reply To Office Action of 05/22/03

Amendments to the Specification:

Please amend without prejudice the Substitute Specification as follows:

Please amend the paragraph beginning at page 2, line 26 as follows:

C1
--Figures 4, [[and]] 5, and 6 show schematic process steps for manufacturing the bidirectional semiconductor component according to the exemplary embodiments of the present invention.--.

Please insert the following paragraph at line 23 at page 3 as follows:

C2
--Thus, the exemplary embodiment is of a bidirectional semiconductor component having two symmetrical MOS transistor structures integrated laterally in a substrate and connected antiseriably, their drain terminals being connected to one another (as indicated in Figure 2), in which a zone (28) having the same type of conductivity as the drain region yet a higher doping than that of the drain region (12) is situated upstream from a pn junction (22) of one of the MOS transistors (26) in a junction area with the drain region (12).--.